



### IXFR38N80Q2 Information



For Reference Only

Part Number IXFR38N80Q2

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 800V 28A ISOPLUS247

Package ISOPLUS247?

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## IXFR38N80Q2 Specifications

Manufacturer Part Number         IXFR38N80Q2           Manufacturer         IXYS           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         ISOPLUS247?           Series         HiPerFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         800V           Current - Continuous Drain (Id) @ 25°C         28A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4.5V @ 8mA           Gate Charge (Qg) (Max) @ Vgs         190nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         \$340pF @ 25V           Vgs (Max)         \$30V           FET Feature         -           Power Dissipation (Max)         416W (Tc)           Rds On (Max) @ Id, Vgs         240 mOhm @ 19A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         ISOPLUS247?           Package / Case         ISOPLUS247?		
CategoryDiscrete Semiconductor ProductsPackageISOPLUS247?SeriesHiPerFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C28A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 8mAGate Charge (Qg) (Max) @ Vgs190nC @ 10VInput Capacitance (Ciss) (Max) @ Vds8340pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)416W (Tc)Rds On (Max) @ Id, Vgs240 mOhm @ 19A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageISOPLUS247?Package / CaseISOPLUS247?	Manufacturer Part Number	IXFR38N80Q2
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Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  28A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  4.5V @ 8mA  Gate Charge (Qg) (Max) @ Vgs  190nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  240 mOhm @ 19A, 10V  Operating Temperature  Supplier Device Package  FEC Sop LUS247?  Package / Case  MOSFET (Metal Oxide)  800V  800V  800V  800V  28A (Tc)  10V  4.5V @ 8mA  4.5V @ 8mA  4.5V @ 8mA  4.5V @ 8mA  4.6W (Tc)  8340pF @ 25V  430V  FET Feature  - Through Hole  Supplier Device Package	Series	HiPerFET?
Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C28A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 8mAGate Charge (Qg) (Max) @ Vgs190nC @ 10VInput Capacitance (Ciss) (Max) @ Vds8340pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)416W (Tc)Rds On (Max) @ Id, Vgs240 mOhm @ 19A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageISOPLUS247?Package / CaseISOPLUS247?	FET Type	N-Channel
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Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  8340pF @ 25V  Vgs (Max)  ### FET Feature  -  Power Dissipation (Max)  Al6W (Tc)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  ISOPLUS247?  Package / Case  ISOPLUS247?	Current - Continuous Drain (Id) @ 25°C	28A (Tc)
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Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package ISOPLUS247?  Package / Case ISOPLUS247?	Power Dissipation (Max)	416W (Tc)
Mounting Type Through Hole Supplier Device Package ISOPLUS247? Package / Case ISOPLUS247?	Rds On (Max) @ Id, Vgs	240 mOhm @ 19A, 10V
Supplier Device Package ISOPLUS247? Package / Case ISOPLUS247?	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case ISOPLUS247?	Mounting Type	Through Hole
	Supplier Device Package	ISOPLUS247?
Report errors?	Package / Case	ISOPLUS247?
		Report errors?

### IXFR38N80Q2 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# IXFR38N80Q2 Payment Methods



















### **IXFR38N80Q2 Shipping Methods**













If you have any question about IXFR38N80Q2, please do not hesitate to contact us!

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